

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Cancelled)
2. (Currently Amended) A method for processing a work piece with a plasma forming component of a process recipe, comprising:
  - providing a process chamber within which the work piece is processed, and which includes at least a first processing zone and a second processing zone, each zone representing a portion of the work piece to be processed;
  - outputting the plasma forming component into the first processing zone of the process chamber without outputting the plasma forming component into the second processing zone of the process chamber;
  - outputting the plasma forming component into the second processing zone of the process chamber without outputting the plasma forming component into the first processing zone of the process chamber; and
  - continuously switching between the step of outputting the plasma forming component into the first processing zone and the step of outputting the plasma forming component into the second processing zone so as to effect the concentration of the plasma forming component between the first and second processing zones while generating or sustaining a plasma within the process chamber.
3. (Previously Presented) The method as recited in claim 2 further including varying the magnitude of the plasma forming component between each of the processing zones such that the magnitude of the plasma forming component at the first processing zone is different than the magnitude of the plasma forming component at the second processing zone.
4. (Previously Presented) The method as recited in claim 2 further including setting the timing of the switching step such that the outputting time at the first processing zone is different than the outputting time at the second processing zone.
5. (Previously Presented) The method as recited in claim 2 further including varying the constituents of the plasma forming component between each of the processing zones such that

the constituents of the plasma forming component at the first processing zone is different than the constituents of the plasma forming component at the second processing zone.

6. (Previously Presented) The method as recited in claim 2 further including varying the ratio of constituents of the plasma forming component between each of the processing zones such that the ratio at the first processing zone is different than the ratio of the plasma forming component at the second processing zone.
7. (Previously Presented) The method as recited in claim 2 further including,
  - varying the magnitude of the plasma forming component between each of the processing zones such that the magnitude of the plasma forming component at the first processing zone is different than the magnitude of the plasma forming component at the second processing zone;
  - varying setting the timing of the switching step such that the outputting time at the first processing zone is different than the outputting time at the second processing zone;
  - varying the constituents of the plasma forming component between each of the processing zones such that the constituents of the plasma forming component at the first processing zone is different than the constituents of the plasma forming component at the second processing zone; and
  - varying the ratio of constituents of the plasma forming component between each of the processing zones such that the ratio at the first processing zone is different than the ratio of the plasma forming component at the second processing zone.
8. (Original) The method as recited in claim 2 wherein the first processing zone corresponds to a center portion of the work piece and the second processing zone corresponds to an outer portion of the work piece.
9. (Previously Presented) The method as recited in claim 2 further including supplying the plasma forming component from a single component source.
10. (Cancelled)
11. (Previously Presented) The method as recited in claim 2 wherein the plasma forming component is energy.

12. (Previously Presented) The method as recited in claim 11 wherein the steps of outputting the plasma forming component includes producing an electric field inside the process chamber.
13. (Previously Presented) The method as recited in claim 2 wherein the plasma forming component is gas.
14. (Previously Presented) The method as recited in claim 2 wherein the steps of outputting the plasma forming component includes releasing a gaseous source material inside the process chamber.
15. (Currently Amended) A method of forming a plasma inside a process chamber, comprising:  
receiving a plasma forming component from a single component source;  
alternately distributing the received plasma forming component between two different regions of the process chamber so as to effect the concentration of the plasma forming component in the different regions of the process chamber while generating or sustaining a plasma continuously within the process chamber.
16. (Original) The method as recited in claim 15 wherein the different regions include an inner region and an outer region.
17. (Original) The method as recited in claim 15 wherein the plasma forming component is gas.
18. (Original) The method as recited in claim 15 wherein the plasma forming component is energy.
19. (Currently Amended) The method as recited in claim 15 further including,  
receiving a second plasma forming component from a second single component source, the second plasma forming component being different than the first plasma forming component; and

alternately distributing the received second plasma forming component between two different regions of the process chamber so as to effect the concentration of the second plasma forming component in the different regions of the process chamber while generating or sustaining a plasma continuously within the process chamber.

20. (Original) The method as recited in claim 19 wherein the first plasma forming component is gas and the second plasma forming component is energy.
21. (Previously Presented) A method for processing a semiconductor substrate, said method comprising:  
continuously delivering plasma forming components to a process chamber;  
via time multiplexing, selectively switching the delivery of the plasma forming components back and forth between a first delivery condition where the plasma forming components are only delivered to an inner region of the process chamber, and a second delivery condition where the plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the plasma forming component in an inner and an outer region of the process chamber, the first delivery condition allowing the plasma forming components to be delivered into an inner region of a process chamber while at the same time preventing the same plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the plasma forming components to be delivered into the outer region of the process chamber while at the same time preventing the same plasma forming components from being delivered into the inner region of the process chamber.
22. (New) The method as recited in claim 12 wherein the electric field is inductively coupled into the process chamber via an external electrode disposed outside the process chamber.
23. (New) The method as recited in claim 19 wherein the distribution of the received first component and the received second component is controlled separately.
24. (New) The method as recited in claim 23 wherein the distribution of the received first component and the received second component follow different time scales.

25. (New) The method as recited in claim 21 wherein the plasma forming components are continuously delivered to a process chamber in order to ignite and sustain a continuous plasma for continuously processing a top surface of the semiconductor substrate.
26. (New) The method as recited in claim 21 wherein the plasma forming component is gas.
27. (New) The method as recited in claim 21 wherein the plasma forming component is energy.
28. (New) The method as recited in claim 21 further including,  
continuously delivering second plasma forming components to the process chamber;  
via a second time multiplexing operation that is separate from the time multiplexing operation associated with the plasma forming components, selectively switching the delivery of the second plasma forming components back and forth between a first delivery condition where the second plasma forming components are only delivered to an inner region of the process chamber, and a second delivery condition where the second plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the second plasma forming component in an inner and an outer region of the process chamber, the first delivery condition allowing the second plasma forming components to be delivered into an inner region of a process chamber while at the same time preventing the same second plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the second plasma forming components to be delivered into the outer region of the process chamber while at the same time preventing the same second plasma forming components from being delivered into the inner region of the process chamber, the plasma forming components corresponding to energy, the second plasma forming components corresponding to gas.
29. (New) The method as recited in claim 2 wherein the plasma forming component is outputted the same distance from the work piece when outputted to the first processing zone and the second processing zone.